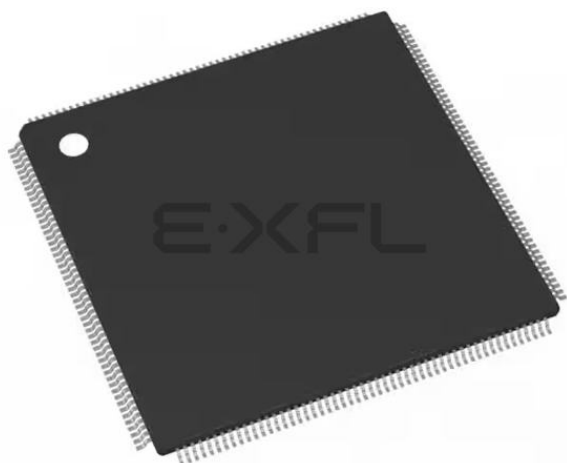




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Details

Product Status	Active
Core Processor	e200z4d
Core Size	32-Bit Single-Core
Speed	125MHz
Connectivity	CANbus, I ² C, LINbus, SCI, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	150
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	1.064M x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 20x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	208-LQFP
Supplier Device Package	208-TQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5645sf1vltr

Package pinouts and signal descriptions

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	
A	PC[15]	PB[2]	PC[13]	PI[1]	PE[7]	PH[8]	PE[2]	PE[4]	PC[4]	PE[3]	PH[9]	PI[4]	PH[11]	PE[14]	PA[10]	PG[11]	A
B	PH[13]	PC[14]	PC[8]	PC[12]	PI[3]	PE[6]	PH[5]	PE[5]	PC[5]	PC[0]	PC[2]	PH[12]	PG[10]	PA[11]	PA[9]	PA[8]	B
C	PH[14]	VDD_HV_A	PC[9]	PL[0]	PI[0]	PH[7]	PH[6]	VSS_LV	VDD_HV_A	PA[5]	PC[3]	PE[15]	PG[14]	PE[12]	PA[7]	PE[13]	C
D	PG[5]	PI[6]	PJ[4]	PB[3]	PK[15]	PI[2]	PH[4]	VDD_LV	PC[1]	PH[10]	PA[6]	PI[5]	PG[15]	PF[14]	PF[15]	PH[2]	D
E	PG[3]	PI[7]	PH[15]	PG[2]									PG[0]	PG[1]	PH[0]	VDD_HV_A	E
F	PA[2]	PG[4]	PA[1]	PE[1]									PH[1]	PH[3]	PG[12]	PG[13]	F
G	PE[8]	PE[0]	PE[10]	PA[0]									VDD_HV_B	PI[13]	PI[12]	PA[3]	G
H	PE[9]	VDD_HV_A	PE[11]	PK[1]									VDD_HV_A	VDD_LV	VSS_LV	PI[11]	H
J	VSS_HV	VRC_CTL	VDD_LV	PG[9]									PD[15]	PI[8]	PI[9]	PI[10]	J
K	RESET	VSS_LV	PG[8]	PC[11]									PD[14]	PD[13]	PB[14]	PB[15]	K
L	PC[10]	PG[7]	PB[0]	PK[2]									PD[12]	PB[12]	PB[13]	VDD_HV_ADC1	L
M	PG[6]	PB[1]	PK[4]	PF[9]									PB[11]	PD[10]	PD[11]	VSS_HV_ADC1	M
N	PK[3]	PF[8]	PC[6]	PC[7]	PJ[13]	VDD_HV_A	PB[10]	PF[6]	VDD_HV_A	PJ[1]	PD[2]	PJ[5]	PB[5]	PB[6]	PJ[6]	PD[9]	N
P	PF[12]	PF[10]	PF[13]	PA[14]	PJ[9]	PA[12]	PF[0]	PF[5]	PF[7]	PJ[3]	PI[15]	PD[4]	PD[7]	PD[8]	PJ[8]	PJ[7]	P
R	PF[11]	PA[15]	PJ[11]	PJ[15]	PA[13]	PF[2]	PF[3]	PF[4]	VDD_LV	PJ[2]	PJ[0]	PD[0]	PD[3]	PD[6]	VDD_HV_ADC0	PB[7]	R
T	PJ[12]	PA[4]	PK[0]	PJ[14]	PJ[10]	PF[1]	XTAL	EXTAL	VSS_LV	PB[9]	PB[8]	PI[14]	PD[1]	PD[5]	VSS_HV_ADC0	PB[4]	T
	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	

Notes:

- 1) VDD_HV_B supplies the IO voltage domain for the pins PE[12], PA[11], PA[10], PA[9], PA[8], PA[7], PE[13], PF[14], PF[15], PG[0], PG[1], PH[3], PH[2], PH[1], PH[0], PG[12], PG[13], and PA[3].
- 2) Availability of port pin alternate functions depends on product selection.

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	
A	PC[15]	PB[2]	PC[13]	PI[1]	PE[7]	PH[8]	PE[2]	PE[4]	PC[4]	PE[3]	PH[9]	PI[4]	PH[11]	PE[14]	PA[10]	PG[11]	A
B	PH[13]	PC[14]	PC[8]	PC[12]	PI[3]	PE[6]	PH[5]	PE[5]	PC[5]	PC[0]	PC[2]	PH[12]	PG[10]	PA[11]	PA[9]	PA[8]	B
C	PH[14]	VDD_HV_A	PC[9]	PL[0]	PI[0]	PH[7]	PH[6]	VSS_LV	VDD_HV_A	PA[5]	PC[3]	PE[15]	PG[14]	PE[12]	PA[7]	PE[13]	C
D	PG[5]	PI[6]	PJ[4]	PB[3]	PK[15]	PI[2]	PH[4]	VDD_LV	PC[1]	PH[10]	PA[6]	PI[5]	PG[15]	PF[14]	PF[15]	PH[2]	D
E	PG[3]	PI[7]	PH[15]	PG[2]	VDD_LV	VSS_LV	PK[10]	PK[9]	PM[1]	PM[0]	PL[15]	PL[14]	PG[0]	PG[1]	PH[0]	VDD_HV_A	E
F	PA[2]	PG[4]	PA[1]	PE[1]	PL[2]	PM[6]	PL[1]	PK[11]	PM[5]	PL[13]	PL[12]	PM[2]	PH[1]	PH[3]	PG[12]	PG[13]	F
G	PE[8]	PE[0]	PE[10]	PA[0]	PL[3]	VSS_HV	VSS_HV	VSS_HV	VSS_HV	VSS_HV	VSS_HV	PK[12]	VDD_HV_B	PI[13]	PI[12]	PA[3]	G
H	PE[9]	VDD_HV_A	PE[11]	PK[1]	PL[4]	VSS_LV	VSS_LV	VSS_HV	VSS_HV	VSS_HV	VSS_HV	PK[13]	VDD_HV_A	VDD_LV	VSS_LV	PI[11]	H
J	VSS_HV	VRC_CTRL	VDD_LV	PG[9]	PL[5]	VSS_LV	VSS_LV	VSS_LV	VSS_HV	VSS_HV	VSS_HV	PK[14]	PD[15]	PI[8]	PI[9]	PI[10]	J
K	RESET	VSS_LV	PG[8]	PC[11]	PL[6]	VSS_LV	VSS_LV	VSS_LV	VSS_LV	VDD_LV	VDD_LV	PM[3]	PD[14]	PD[13]	PB[14]	PB[15]	K
L	PC[10]	PG[7]	PB[0]	PK[2]	PL[7]	VSS_LV	VSS_LV	VSS_LV	VSS_LV	VDD_LV	VDD_LV	PM[4]	PD[12]	PB[12]	PB[13]	VDD_HV_ADC1	L
M	PG[6]	PB[1]	PK[4]	PF[9]	PK[5]	PK[6]	PK[7]	PK[8]	PL[8]	PL[9]	PL[10]	PL[11]	PB[11]	PD[10]	PD[11]	VSS_HV_ADC1	M
N	PK[3]	PF[8]	PC[6]	PC[7]	PJ[13]	VDD_HV_A	PB[10]	PF[6]	VDD_HV_A	PJ[1]	PD[2]	PJ[5]	PB[5]	PB[6]	PJ[6]	PD[9]	N
P	PF[12]	PF[10]	PF[13]	PA[14]	PJ[9]	PA[12]	PF[0]	PF[5]	PF[7]	PJ[3]	PI[15]	PD[4]	PD[7]	PD[8]	PJ[8]	PJ[7]	P
R	PF[11]	PA[15]	PJ[11]	PJ[15]	PA[13]	PF[2]	PF[3]	PF[4]	VDD_LV	PJ[2]	PJ[0]	PD[0]	PD[3]	PD[6]	VDD_HV_ADC0	PB[7]	R
T	PJ[12]	PA[4]	PK[0]	PJ[14]	PJ[10]	PF[1]	XTAL	EXTAL	VSS_LV	PB[9]	PB[8]	PI[14]	PD[1]	PD[5]	VSS_HV_ADC0	PB[4]	T
	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	

Notes:

- 1) VDD_HV_B supplies the IO voltage domain for the pins PE[12], PA[11], PA[10], PA[9], PA[8], PA[7], PE[13], PF[14], PF[15], PG[0], PG[1], PH[3], PH[2], PH[1], PH[0], PG[12], PG[13], PA[3], PM[3], and PM[4].
- 2) Availability of port pin alternate functions depends on product selection.

Figure 4. 256-pin BGA configuration

3.1 Pad types

In the device the following types of pads are available for system pins and functional port pins:

S = Slow¹

M = Medium^{1, 2}

1. See the I/O pad electrical characteristics in the device data sheet for details.
2. All medium and fast pads are in slow configuration by default at reset and can be configured as fast or medium. For example, Fast/Medium pad will be Medium by default at reset. Similarly, Slow/Medium pad will be Slow by default. Only exception is PC[1] which is in medium configuration by default (refer to PCR.SRC in the reference manual, Pad Configuration Registers (PCR0—PCR198)).

Package pinouts and signal descriptions

F = Fast^{1, 2}

I = Input only with analog feature¹

A = Analog

3.2 System pins

The system pins are listed in Table 3.

Table 3. System pin descriptions

Port pin	Function	I/O direction	Pad type	RESET config.	Pin number		
					176 LQFP	208 LQFP	256 MAPBGA
RESET	Bidirectional reset with Schmitt-Trigger characteristics and noise filter.	I/O	M	Input, weak pull-up only after PHASE2	29	29	K1
EXTAL	Analog input of the oscillator amplifier circuit. Needs to be grounded if oscillator bypass mode is used.	I	A ¹	—	58	74	T8
XTAL	Analog output of the oscillator amplifier circuit, when the oscillator is not in bypass mode. Analog input for the clock generator when the oscillator is in bypass mode.	I/O	A ¹	—	56	72	T7

NOTES:

¹ For analog pads, it is not recommended to enable IBE if APC is enabled to avoid extra current in middle range voltage.

3.3 Functional ports

The functional port pins are listed in Table 4.

Table 4. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function ¹	Function	Peripheral	I/O direction ²	Pad type	RESET config.	Pin number		
								176 LQFP	208 LQFP	256 MAPBGA
PD[8]	PCR[56]	AF0	GPI[56]	SIUL	I	I	Tristate	87	103	P14
		AF1	—	—	—					
		AF2	—	—	—					
		AF3	—	—	—					
		—	ADC0_P[12]	ADC_0	I					
		—	ADC1_P[12]	ADC_1	I					
PD[9]	PCR[57]	AF0	GPI[57]	SIUL	I	I	Tristate	94	114	N16
		AF1	—	—	—					
		AF2	—	—	—					
		AF3	—	—	—					
		—	ADC0_P[13]	ADC_0	I					
		—	ADC1_P[13]	ADC_1	I					
PD[10]	PCR[58]	AF0	GPI[58]	SIUL	I	I	Tristate	95	115	M14
		AF1	—	—	—					
		AF2	—	—	—					
		AF3	—	—	—					
		—	ADC0_P[14]	ADC_0	I					
		—	ADC1_P[14]	ADC_1	I					
PD[11]	PCR[59]	AF0	GPI[59]	SIUL	I	I	Tristate	96	116	M15
		AF1	—	—	—					
		AF2	—	—	—					
		AF3	—	—	—					
		—	ADC0_P[15]	ADC_0	I					
		—	ADC1_P[15]	ADC_1	I					
PD[12]	PCR[60]	AF0	GPIO[60]	SIUL	I/O	S	Tristate	100	120	L13
		AF1	CS5_0	DSPI_0	O					
		AF2	E0UC[24]	eMIOS_0	I/O					
		AF3	—	—	—					
		—	ADC0_S[4]	ADC_0	I					
		—	—	—	—					
PD[13]	PCR[61]	AF0	GPIO[61]	SIUL	I/O	S	Tristate	102	124	K14
		AF1	CS0_1	DSPI_1	I/O					
		AF2	E0UC[25]	eMIOS_0	I/O					
		AF3	—	—	—					
		—	ADC0_S[5]	ADC_0	I					
		—	—	—	—					
PD[14]	PCR[62]	AF0	GPIO[62]	SIUL	I/O	S	Tristate	104	126	K13
		AF1	CS1_1	DSPI_1	O					
		AF2	E0UC[26]	eMIOS_0	I/O					
		AF3	—	—	—					
		ALT4	FR_DBG[0]	Flexray	O					
		—	ADC0_S[6]	ADC_0	I					

Table 4. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function ¹	Function	Peripheral	I/O direction ²	Pad type	RESET config.	Pin number		
								176 LQFP	208 LQFP	256 MAPBGA
PH[14]	PCR[126]	AF0 AF1 AF2 AF3	GPIO[126] SCK_4 CS1_3 E1UC[27]	SIUL DSPI_4 DSPI_3 eMIOS_1	I/O I/O O I/O	M/S	Tristate	10	10	C1
PH[15]	PCR[127]	AF0 AF1 AF2 AF3	GPIO[127] SOUT_5 — E1UC[17]	SIUL DSPI_5 — eMIOS_1	I/O O — I/O	M/S	Tristate	8	8	E3
PI[0]	PCR[128]	AF0 AF1 AF2 AF3	GPIO[128] E0UC[28] LIN8TX —	SIUL eMIOS_0 LINFlexD_8 —	I/O I/O O —	S	Tristate	172	196	C5
PI[1]	PCR[129]	AF0 AF1 AF2 AF3 — —	GPIO[129] E0UC[29] — — WKPU[24] LIN8RX	SIUL eMIOS_0 — — WKPU LINFlexD_8	I/O I/O — — I I	S	Tristate	171	195	A4
PI[2]	PCR[130]	AF0 AF1 AF2 AF3	GPIO[130] E0UC[30] LIN9TX —	SIUL eMIOS_0 LINFlexD_9 —	I/O I/O O —	S	Tristate	170	194	D6
PI[3]	PCR[131]	AF0 AF1 AF2 AF3 — —	GPIO[131] E0UC[31] — — WKPU[23] LIN9RX	SIUL eMIOS_0 — — WKPU LINFlexD_9	I/O I/O — — I I	S	Tristate	169	193	B5
PI[4]	PCR[132]	AF0 AF1 AF2 AF3	GPIO[132] E1UC[28] SOUT_4 —	SIUL eMIOS_1 DSPI_4 —	I/O I/O O —	M/S	Tristate	143	167	A12
PI[5]	PCR[133]	AF0 AF1 AF2 AF3 ALT4	GPIO[133] E1UC[29] SCK_4 CS2_5 CS2_6	SIUL eMIOS_1 DSPI_4 DSPI_5 DSPI_6	I/O I/O I/O O O	M/S	Tristate	142	166	D12
PI[6]	PCR[134]	AF0 AF1 AF2 AF3 ALT4	GPIO[134] E1UC[30] CS0_4 CS0_5 CS0_6	SIUL eMIOS_1 DSPI_4 DSPI_5 DSPI_6	I/O I/O I/O I/O I/O	S	Tristate	11	11	D2

Table 4. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function ¹	Function	Peripheral	I/O direction ²	Pad type	RESET config.	Pin number		
								176 LQFP	208 LQFP	256 MAPBGA
PJ[7]	PCR[151]	AF0 AF1 AF2 AF3 —	GPIO[151] — — — ADC0_S[30]	SIUL — — — ADC_0	I/O — — — I	S	Tristate	—	111	P16
PJ[8]	PCR[152]	AF0 AF1 AF2 AF3 —	GPIO[152] — — — ADC0_S[31]	SIUL — — — ADC_0	I/O — — — I	S	Tristate	—	110	P15
PJ[9]	PCR[153]	AF0 AF1 AF2 AF3 —	GPIO[153] — — — ADC1_S[8]	SIUL — — — ADC_1	I/O — — — I	S	Tristate	—	68	P5
PJ[10]	PCR[154]	AF0 AF1 AF2 AF3 —	GPIO[154] — — — ADC1_S[9]	SIUL — — — ADC_1	I/O — — — I	S	Tristate	—	67	T5
PJ[11]	PCR[155]	AF0 AF1 AF2 AF3 —	GPIO[155] — — — ADC1_S[10]	SIUL — — — ADC_1	I/O — — — I	S	Tristate	—	60	R3
PJ[12]	PCR[156]	AF0 AF1 AF2 AF3 —	GPIO[156] — — — ADC1_S[11]	SIUL — — — ADC_1	I/O — — — I	S	Tristate	—	59	T1
PJ[13]	PCR[157]	AF0 AF1 AF2 AF3 — — — —	GPIO[157] — CS1_7 — CAN4RX ADC1_S[12] CAN1RX WKPU[31]	SIUL — DSPI_7 — FlexCAN_4 ADC_1 FlexCAN_1 WKPU	I/O — O — I I I I	S	Tristate	—	65	N5
PJ[14]	PCR[158]	AF0 AF1 AF2 AF3	GPIO[158] CAN1TX CAN4TX CS2_7	SIUL FlexCAN_1 FlexCAN_4 DSPI_7	I/O O O O	M/S	Tristate	—	64	T4

- ⁴ This voltage is internally generated by the device and no external voltage should be supplied.
- ⁵ 100 nF capacitance needs to be provided between $V_{DD_HV_ADC0/ADC1}/V_{SS_HV_ADC0/ADC1}$ pair.
- ⁶ Both the relative and the fixed conditions must be met. For instance: If $V_{DD_HV_A}$ is 5.9 V, $V_{DD_HV_ADC0}$ maximum value is 6.0 V then, despite the relative condition, the max value is $V_{DD_HV_A} + 0.3 = 6.2$ V.
- ⁷ PA3, PA7, PA10, PA11 and PE12 ADC_1 channels are coming from $V_{DD_HV_B}$ domain hence $V_{DD_HV_ADC1}$ should be within ± 100 mV of $V_{DD_HV_B}$ when these channels are used for ADC_1.
- ⁸ Guaranteed by device validation.

NOTE

SRAM retention guaranteed to LVD levels.

4.5 Thermal characteristics

4.5.1 Package thermal characteristics

Table 11. LQFP thermal characteristics¹

Symbol	C	Parameter	Conditions ²	Pin count	Value ³			Unit
					Min	Typ	Max	
R _{θJA}	CC	D	Thermal resistance, junction-to-ambient natural convection ⁴	Single-layer board—1s	176	—	38 ⁵	°C/W
					208	—	41 ⁶	°C/W
R _{θJA}	CC	D	Thermal resistance, junction-to-ambient natural convection ⁷	Four-layer board—2s2p ⁷	176	—	31	°C/W
					208	—	34	°C/W

NOTES:

¹ Thermal characteristics are targets based on simulation that are subject to change per device characterization.

² $V_{DD} = 3.3 \text{ V} \pm 10\% / 5.0 \text{ V} \pm 10\%$, $T_A = -40$ to 125 °C.

³ All values need to be confirmed during device validation.

⁴ Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.

⁵ Junction-to-Ambient thermal resistance determined per JEDEC JESD51-3 and JESD51-6.

⁶ Junction-to-Ambient thermal resistance determined per JEDEC JESD51-2 and JESD51-6

⁷ Junction-to-Board thermal resistance determined per JEDEC JESD51-8.

Table 12. 256 MAPBGA thermal characteristics¹

Symbol	C	Parameter	Conditions	Value	Unit
R _{θJA}	CC	Thermal resistance, junction-to-ambient natural convection	Single-layer board—1s	43 ²	°C/W
			Four-layer board—2s2p	26 ³	

NOTES:

¹ Thermal characteristics are targets based on simulation that are subject to change per device characterization.

² Junction-to-ambient thermal resistance determined per JEDEC JESD51-2 with the single layer board horizontal. Board meets JESD51-9 specification.

³ Junction-to-ambient thermal resistance determined per JEDEC JESD51-6 with the board horizontal.

4.5.2 Power considerations

The average chip-junction temperature, T_J , in degrees Celsius, may be calculated using Equation 1:

$$T_J = T_A + (P_D \times R_{\theta JA}) \quad \text{Eqn. 1}$$

Where:

T_A is the ambient temperature in °C.

$R_{\theta JA}$ is the package junction-to-ambient thermal resistance, in °C/W.

P_D is the sum of P_{INT} and $P_{I/O}$ ($P_D = P_{INT} + P_{I/O}$).

P_{INT} is the product of I_{DD} and V_{DD} , expressed in watts. This is the chip internal power.

$P_{I/O}$ represents the power dissipation on input and output pins; user determined.

Most of the time for the applications, $P_{I/O} < P_{INT}$ and may be neglected. On the other hand, $P_{I/O}$ may be significant, if the device is configured to continuously drive external modules and/or memories.

An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is given by:

$$P_D = K / (T_J + 273 \text{ °C}) \quad \text{Eqn. 2}$$

Therefore, solving equations 1 and 2:

$$K = P_D \times (T_A + 273 \text{ °C}) + R_{\theta JA} \times P_D^2 \quad \text{Eqn. 3}$$

Where:

K is a constant for the particular part, which may be determined from Equation 3 by measuring P_D (at equilibrium) for a known T_A . Using this value of K , the values of P_D and T_J may be obtained by solving equations 1 and 2 iteratively for any value of T_A .

4.6 I/O pad electrical characteristics

4.6.1 I/O pad types

The device provides four main I/O pad types depending on the associated alternate functions:

- Slow pads—These pads are the most common pads, providing a good compromise between transition time and low electromagnetic emission.
- Medium pads—These pads provide transition fast enough for the serial communication channels with controlled current to reduce electromagnetic emission.
- Fast pads—These pads provide maximum speed. These are used for improved Nexus debugging capability.
- Input only pads—These pads are associated to ADC channels and 32 kHz low power external crystal oscillator providing low input leakage.
- Low power pads—These pads are active in standby mode for wakeup source.

Also, medium/slow and fast/medium pads are available in design which can be configured to behave like a slow/medium and medium/fast pads depending upon the slew-rate control.

Table 15. SLOW configuration output buffer electrical characteristics (continued)

Symbol	C	Parameter	Conditions ^{1,2}	Value			Unit
				Min	Typ	Max	
V _{OL}	CC	P	Push Pull	I _{OL} = 3 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	0.1V _{DD}
		C		I _{OL} = 3 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 1 ⁽³⁾	—	—	0.1V _{DD}
		P		I _{OL} = 1.5 mA, V _{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	0.5

NOTES:

¹ V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = -40 to 125 °C, unless otherwise specified.

² V_{DD} as mentioned in the table is V_{DD_HV_A}/V_{DD_HV_B}.

³ The configuration PAD3V5 = 1 when V_{DD} = 5 V is only a transient configuration during power-up. All pads but RESET and Nexus output (MDOx, EVTO, MCKO) are configured in input or in high impedance state.

Table 16. MEDIUM configuration output buffer electrical characteristics

Symbol	C	Parameter	Conditions ^{1,2}	Value			Unit
				Min	Typ	Max	
V _{OH}	CC	C	Push Pull	I _{OH} = -3 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 0	0.8V _{DD}	—	V
		C		I _{OH} = -1.5 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 1 ³	0.8V _{DD}	—	
		C		I _{OH} = -2 mA, V _{DD} = 3.3 V ± 10%, PAD3V5V = 1	V _{DD} - 0.8	—	
V _{OL}	CC	C	Push Pull	I _{OL} = 3 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	V
		C		I _{OL} = 1.5 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 1 ⁽³⁾	—	—	
		C		I _{OL} = 2 mA, V _{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	

NOTES:

¹ V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = -40 to 125 °C, unless otherwise specified.

² V_{DD} as mentioned in the table is V_{DD_HV_A}/V_{DD_HV_B}.

³ The configuration PAD3V5 = 1 when V_{DD} = 5 V is only a transient configuration during power-up. All pads but RESET and Nexus output (MDOx, EVTO, MCKO) are configured in input or in high impedance state.

Table 17. FAST configuration output buffer electrical characteristics

Symbol		C	Parameter	Conditions ^{1,2}		Value			Unit
						Min	Typ	Max	
V _{OH}	CC	P	Output high level FAST configuration	Push Pull	I _{OH} = -14 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 0	0.8V _{DD}	—	—	V
		C			I _{OH} = -7 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 1 ³	0.8V _{DD}	—	—	
		C			I _{OH} = -11 mA, V _{DD} = 3.3 V ± 10%, PAD3V5V = 1	V _{DD} - 0.8	—	—	
V _{OL}	CC	P	Output low level FAST configuration	Push Pull	I _{OL} = 14 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	0.1V _{DD}	V
		C			I _{OL} = 7 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 1 ⁽³⁾	—	—	0.1V _{DD}	
		C			I _{OL} = 11 mA, V _{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	0.5	

NOTES:

¹ V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = -40 to 125 °C, unless otherwise specified.

² V_{DD} as mentioned in the table is V_{DD_HV_A}/V_{DD_HV_B}.

³ The configuration PAD3V5 = 1 when V_{DD} = 5 V is only a transient configuration during power-up. All pads but RESET and Nexus outputs (MDOx, EVTO, MCKO) are configured in input or in high impedance state.

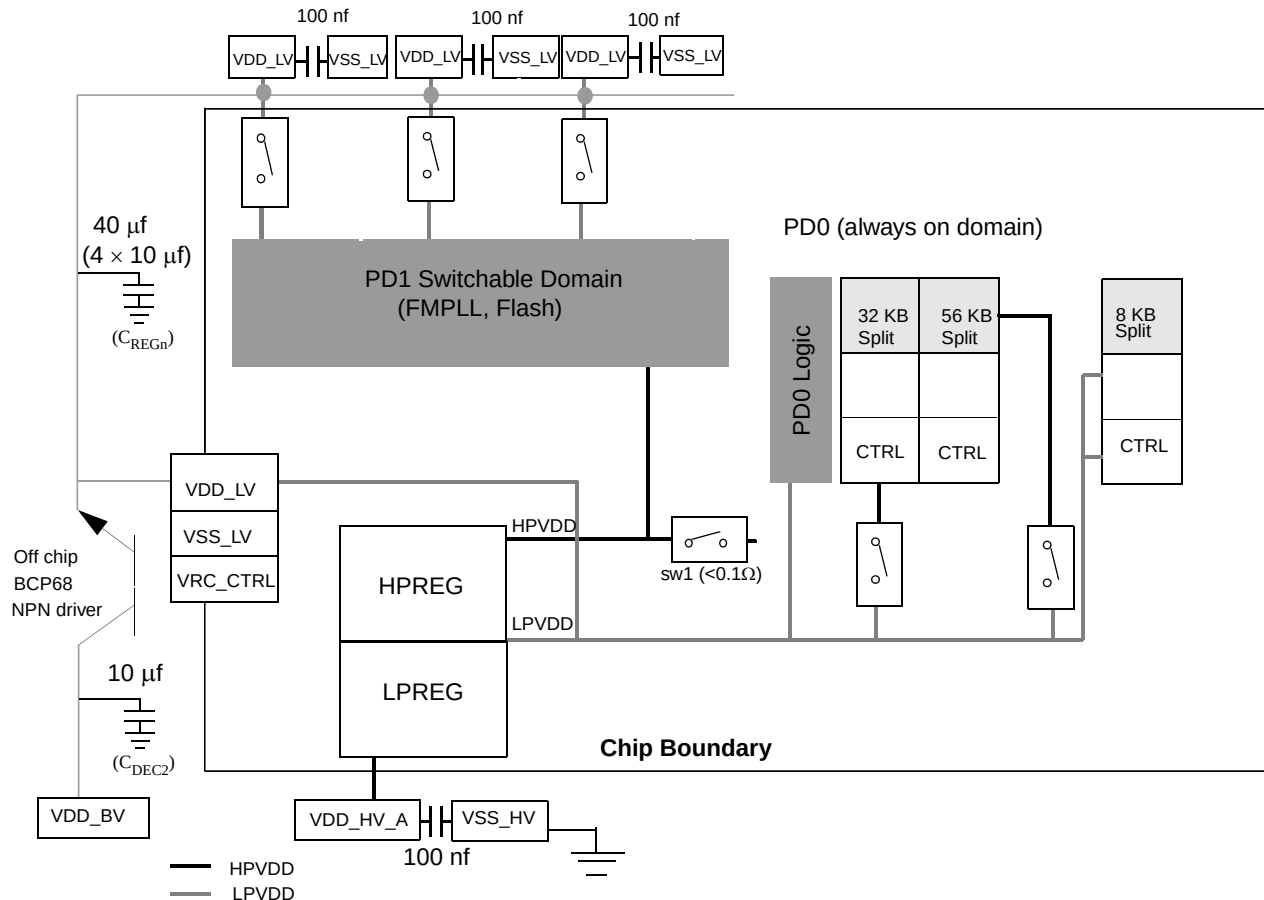
4.6.4 Output pin transition times

Table 18. Output pin transition times

Symbol		C	Parameter	Conditions ^{1,2}		Value ³			Unit
						Min	Typ	Max	
T _{tr}	CC	D	Output transition time output pin ⁴ SLOW configuration	C _L = 25 pF	V _{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	50	ns
		T		C _L = 50 pF		—	—	100	
		D		C _L = 100 pF		—	—	125	
		D		C _L = 25 pF	V _{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	40	
		T		C _L = 50 pF		—	—	50	
		D		C _L = 100 pF		—	—	75	

Electrical Characteristics

- LV_CFLA0/CFLA1: Low voltage supply for the two code Flash modules. It is shorted with LV_COR through double bonding.
- LV_DFLA: Low voltage supply for data Flash module. It is shorted with LV_COR through double bonding.
- LV_PLL: Low voltage supply for FMPLL. It is shorted to LV_COR through double bonding.



1) All VSS_LV pins must be grounded, as shown for VSS_HV pin.

Figure 8. Voltage regulator capacitance connection

The internal voltage regulator requires external bulk capacitance (C_{REGn}) to be connected to the device to provide a stable low voltage digital supply to the device. Also required for stability is the C_{DEC2} capacitor at ballast collector. This is needed to minimize sharp injection current when ballast is turning ON. Apart from the bulk capacitance, user should connect EMI/decoupling cap (C_{REGP}) at each V_{DD_LV}/V_{SS_LV} pin pair.

4.8.1.1 Recommendations

- The external NPN driver must be BCP68 type.
- V_{DD_LV} should be implemented as a power plane from the emitter of the ballast transistor.

Electrical Characteristics

NOTES:

- ¹ All ESD testing is in conformity with CDF-AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits.
- ² A device will be defined as a failure if after exposure to ESD pulses the device no longer meets the device specification requirements. Complete DC parametric and functional testing shall be performed per applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.
- ³ Data based on characterization results, not tested in production.

4.11.3.2 Static latch-up (LU)

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply over-voltage is applied to each power supply pin.
- A current injection is applied to each input, output and configurable I/O pin.

These tests are compliant with the EIA/JESD 78 IC latch-up standard.

Table 33. Latch-up results

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = 125\text{ °C}$ conforming to JESD 78	II level A

4.12 Fast external crystal oscillator (4–40 MHz) electrical characteristics

The device provides an oscillator/resonator driver. Figure 10 describes a simple model of the internal oscillator driver and provides an example of a connection for an oscillator or a resonator.

Table 34 provides the parameter description of 4 MHz to 40 MHz crystals used for the design simulations.

Table 43. Conversion characteristics (12-bit ADC_1)

Symbol		C	Parameter	Conditions ¹	Value			Unit
					Min	Typ	Max	
V _{SS_ADC1}	SR	—	Voltage on VSS_HV_ADC1 (ADC_1 reference) pin with respect to ground (V _{SS_HV}) ²	—	−0.1		0.1	V
V _{DD_ADC1} ³	SR	—	Voltage on VDD_HV_ADC1 pin (ADC_1 reference) with respect to ground (V _{SS_HV})	—	V _{DD_HV_A} − 0.1		V _{DD_HV_A} + 0.1	V
V _{AINx} ^{3,4}	SR	—	Analog input voltage ⁵	—	V _{SS_ADC1} − 0.1		V _{DD_ADC1} + 0.1	V
f _{ADC1}	SR	—	ADC_1 analog frequency	—	8 + 2%		32 + 2%	MHz
t _{ADC1_PU}	SR	—	ADC_1 power up delay	—	1.5			μs
t _{ADC1_S}	CC	T	Sample time ⁶ VDD=5.0 V	—	440			ns
			Sample time ⁽⁶⁾ VDD=3.3 V	—	530			
t _{ADC1_C}	CC	P	Conversion time ^{7, 8} VDD=5.0 V	f _{ADC1} = 32 MHz	2			μs
			Conversion time ^{(7), (6)} VDD =5.0 V	f _{ADC1} = 30 MHz	2.1			
			Conversion time ^{(7), (6)} VDD=3.3 V	f _{ADC1} = 20 MHz	3			
			Conversion time ^{(7), (6)} VDD =3.3 V	f _{ADC1} = 15 MHz	3.01			
C _S	CC	D	ADC_1 input sampling capacitance	—	5			pF
C _{P1}	CC	D	ADC_1 input pin capacitance 1	—	3			pF
C _{P2}	CC	D	ADC_1 input pin capacitance 2	—	1			pF
C _{P3}	CC	D	ADC_1 input pin capacitance 3	—	1.5			pF
R _{SW1}	CC	D	Internal resistance of analog source	—			1	kΩ

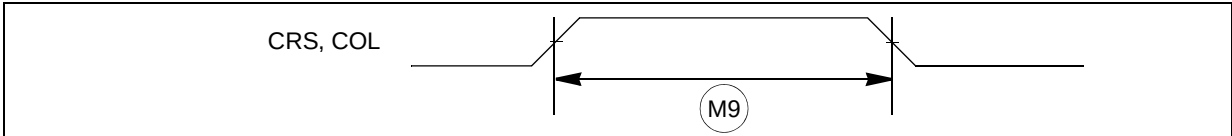


Figure 23. MII async inputs timing diagram

4.18.4 MII Serial Management Channel Timing (MDIO and MDC)

The FEC functions correctly with a maximum MDC frequency of 2.5 MHz.

Table 47. MII serial management channel timing¹

Spec	Characteristic	Min	Max	Unit
M10	MDC falling edge to MDIO output invalid (minimum propagation delay)	0	—	ns
M11	MDC falling edge to MDIO output valid (max prop delay)	—	25	ns
M12	MDIO (input) to MDC rising edge setup	28	—	ns
M13	MDIO (input) to MDC rising edge hold	0	—	ns
M14	MDC pulse width high	40%	60%	MDC period
M15	MDC pulse width low	40%	60%	MDC period

NOTES:

¹ Output pads configured with SRE = 0b11.

Table 48. On-chip peripherals current consumption¹

Symbol	C	Parameter	Conditions		Value ²	Unit
					Typ	
IDD_HV_ADC1	CC	D ADC_1 supply current on V _{DD_HV_ADC1}	V _{DD} = 5.5 V	Analog static consumption (no conversion)	300 × f _{periph}	μA
			V _{DD} = 5.5 V	Analog dynamic consumption (continuous conversion)	6	mA
I _{DD_HV(FLASH)}	CC	D CFlash + DFlash supply current on V _{DD_HV_ADC}	V _{DD} = 5.5 V	—	13.25	mA
I _{DD_HV(PLL)}	CC	D PLL supply current on V _{DD_HV}	V _{DD} = 5.5 V	—	0.0031 × f _{periph}	

NOTES:

¹ Operating conditions: T_A = 25 °C, f_{periph} = 8 MHz to 120 MHz.

² f_{periph} is in absolute value.

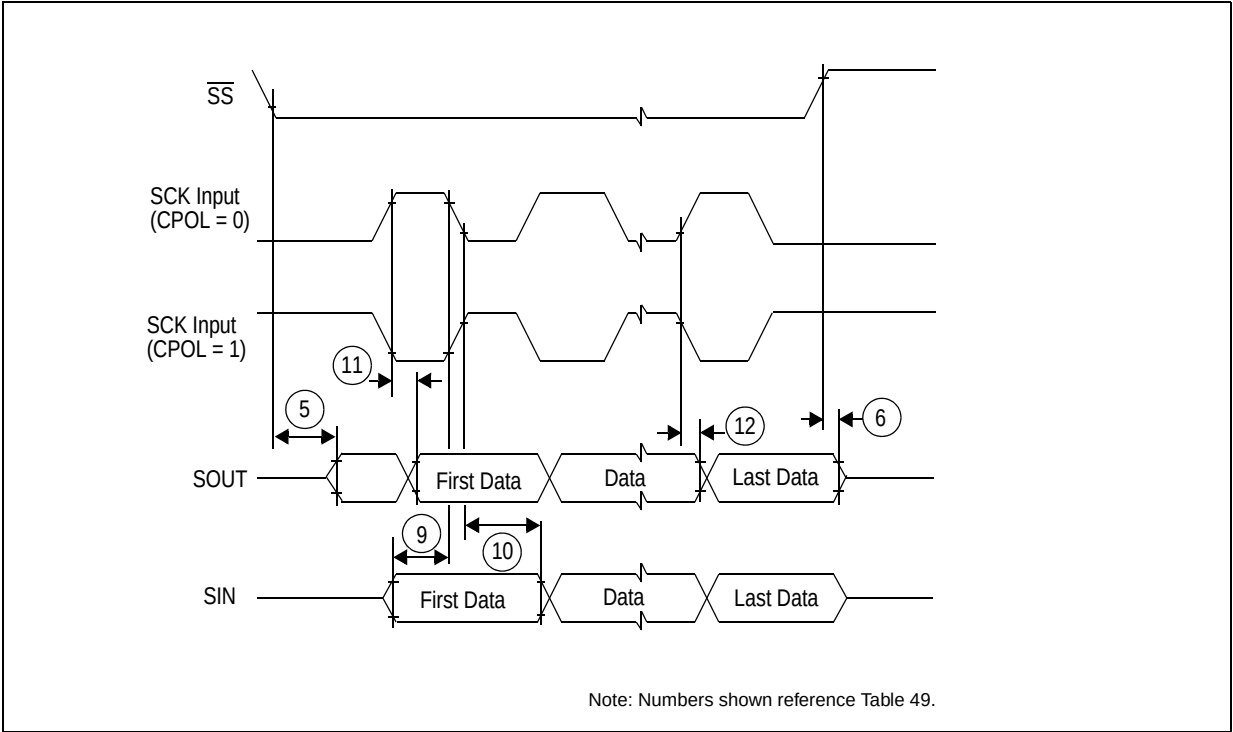


Figure 28. DSPI classic SPI timing–slave, CPHA = 1

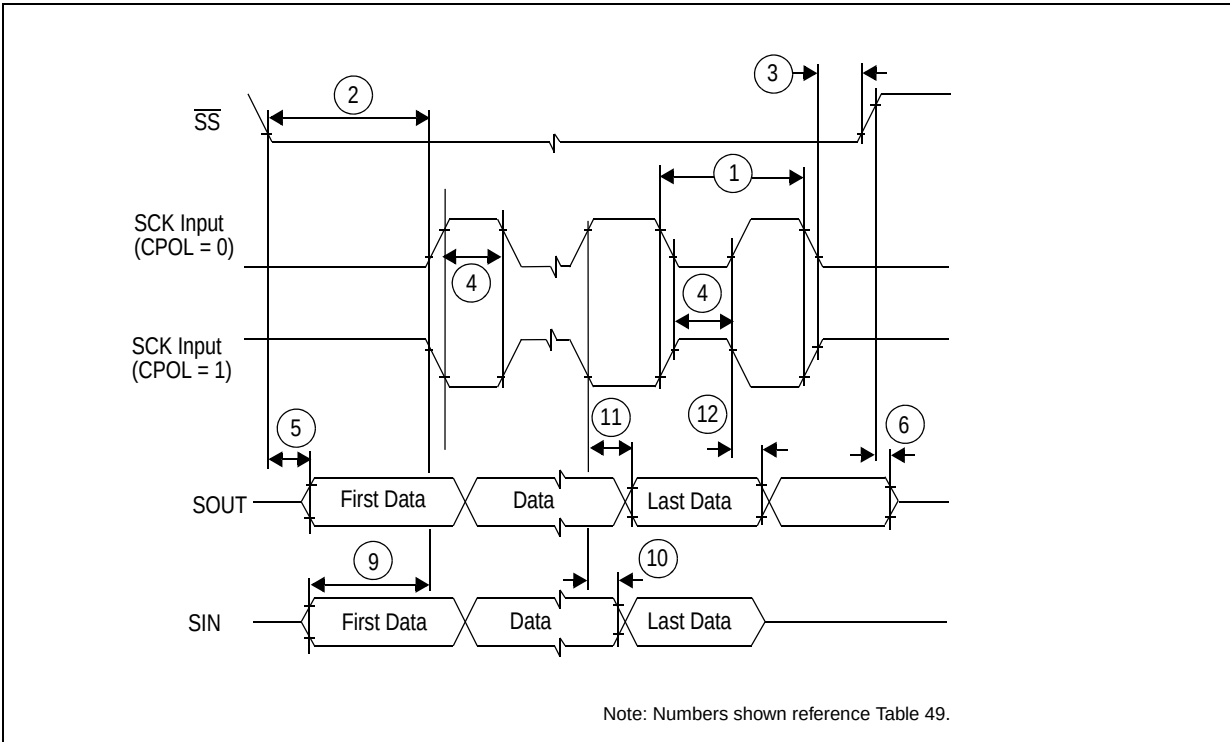


Figure 31. DSPI modified transfer format timing-slave, CPHA = 0

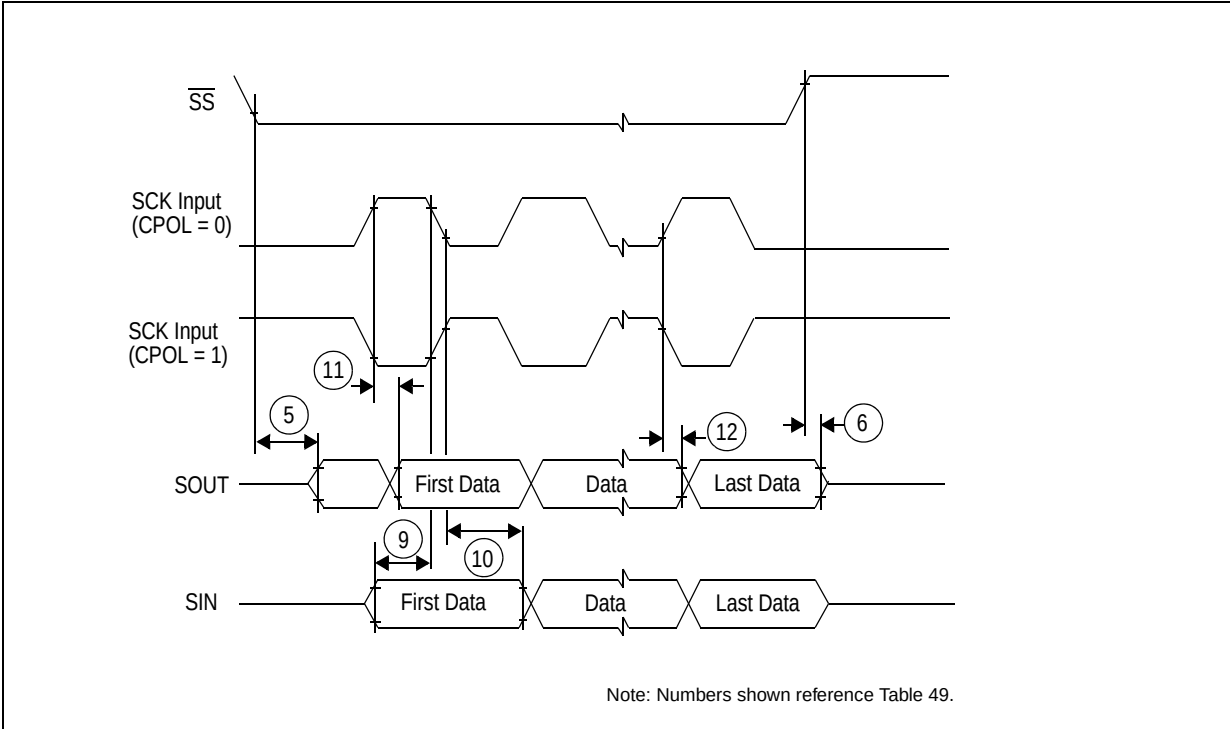


Figure 32. DSPI modified transfer format timing-slave, CPHA = 1

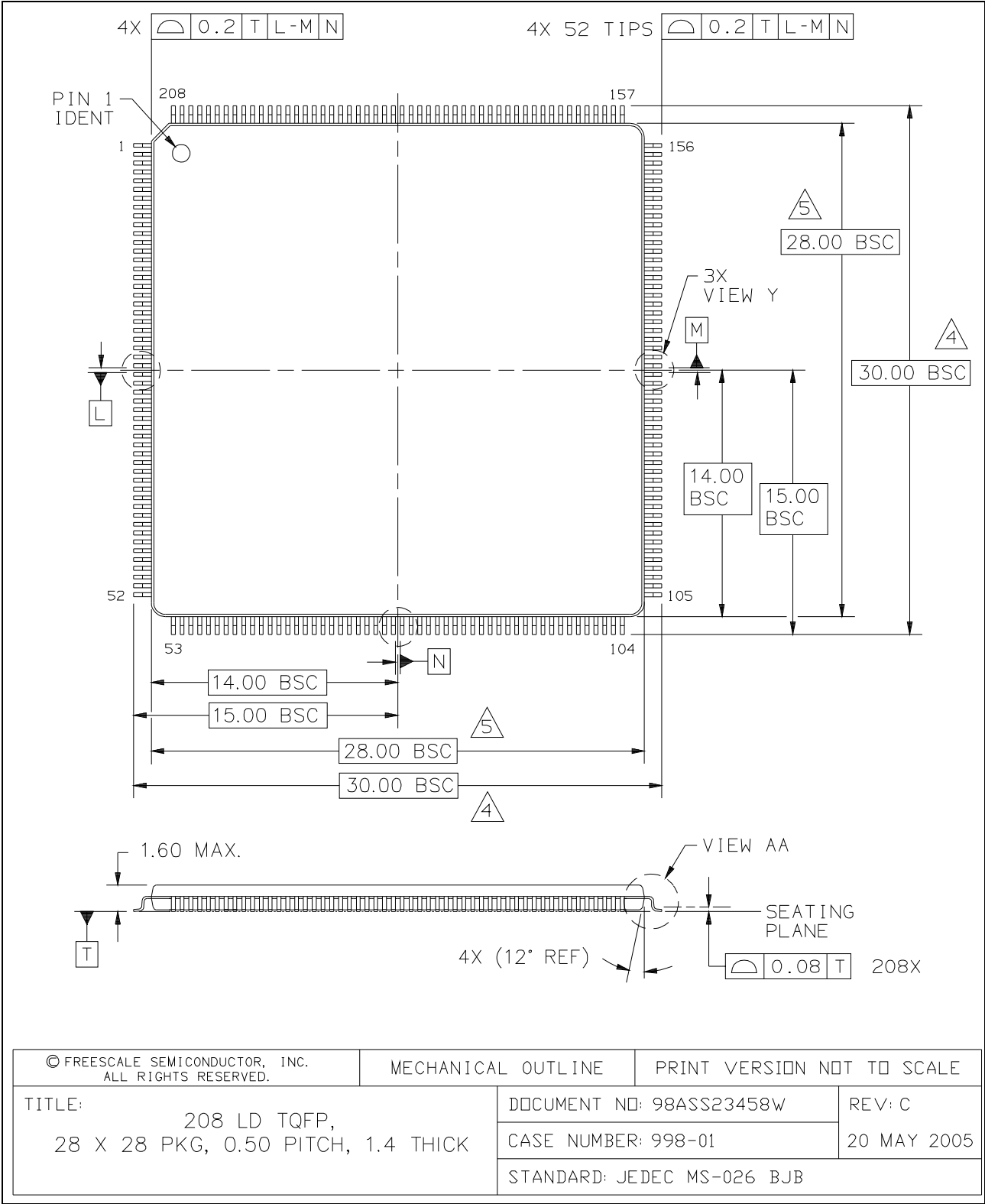


Figure 40. 208 LQFP mechanical drawing (Part 1 of 3)

Figure 44. 256 MAPBGA mechanical drawing (Part 2 of 2)

6 Ordering information

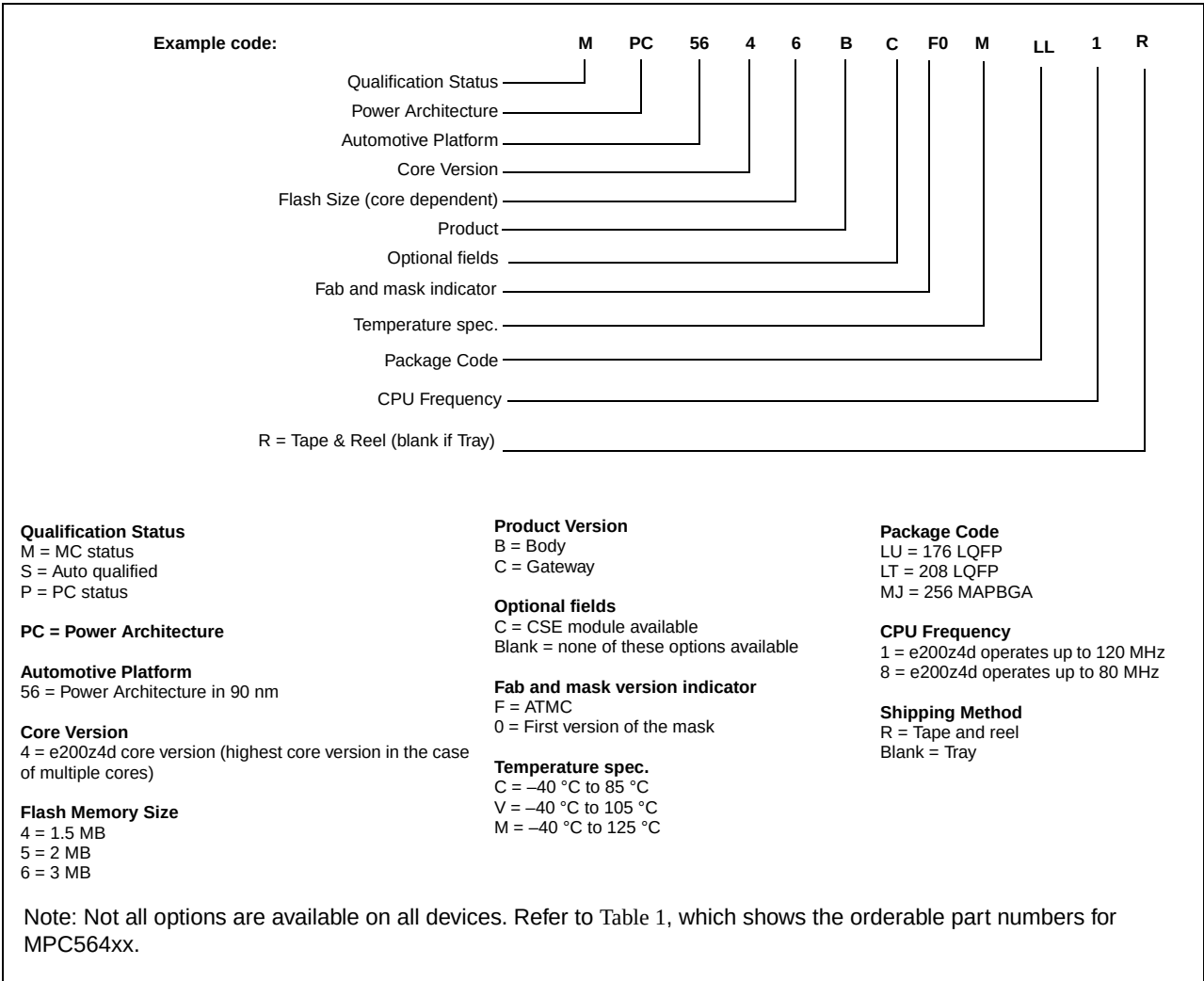


Figure 45. Orderable parts